## NSN 5961-01-626-5741

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View Online at https://aerobasegroup.com/nsn/5961-01-626-5741 **Inclosure Material:** Ceramic **Overall Length:** 0.840 inches **Overall Height:** 0.290 inches **Overall Width:** 0.300 inches **End Application:** Apx113 **Response Time:** 5.0 nanoseconds 1st semiconductor device diode **Component Name And Quantity:** 8 semiconductor device diode **Mounting Method:** Press fit **Semiconductor Material:** Silicon 1st semiconductor device diode Voltage Rating In Volts Per Characteristic: 75.0 reverse breakdown voltage, dc 1st semiconductor device diode **Voltage Tolerance In Percent:** -0.1 to 20.0 1st semiconductor device diode **Current Rating Per Characteristic:** 300.0 milliamperes average forward current averaged over a full 60-hz cycle 1st semiconductor device diode **Power Rating Per Characteristic:** 300.0 milliwatts total power dissipation 1st semiconductor device diode **Capacitance Rating In Picofarads:** 4.0 1st semiconductor device diode **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius ambient air **Product Name:** 1n6101 diode array **Special Features:** Diode array has 8 fast switching speed diodes used for a variety of clamping and mixing applications **Terminal Type And Quantity:** 16 pin Shelf Life: N/a **Unit Of Measure:** 

No

**Demilitarization:** 

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